

Low voltage fast-switching NPN power transistor

Datasheet - production data

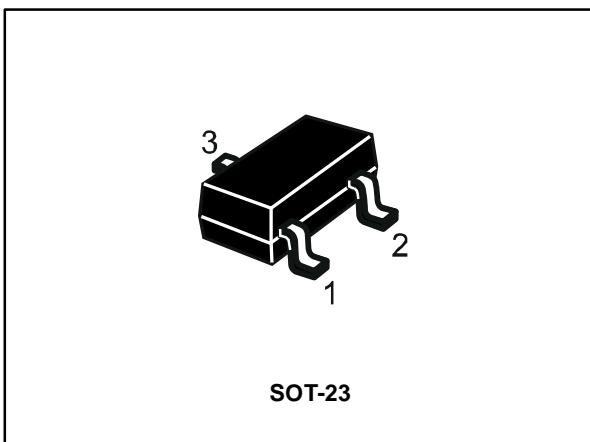
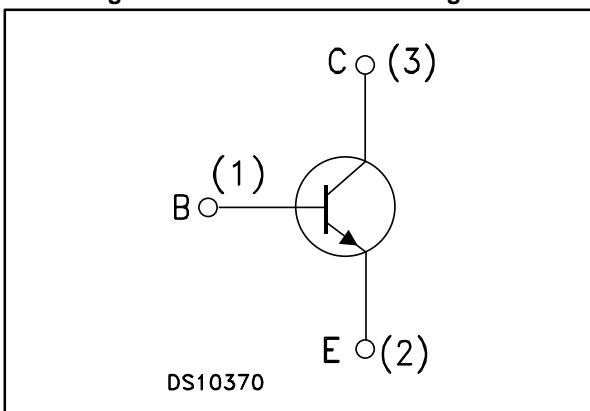


Figure 1: Internal schematic diagram



Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits

Description

The device is a NPN transistor manufactured using new "PB-HCD" (Power Bipolar High Current Density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage.

The complementary PNP is the 2STR2160.

Applications

- LED
- Battery charger
- Motor and relay driver
- Voltage regulation

Table 1: Device summary

Order code	Marking	Package	Packing
2STR1160	1160	SOT-23	Tape and reel

1 Electrical ratings

Table 2: Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-base voltage ($I_E = 0$)	60	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	60	V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	5	V
I_C	Collector current	1	A
I_{CM}	Collector peak current ($t_P < 5\text{ms}$)	2	A
P_{tot}	Total dissipation at $T_{amb} = 25^\circ\text{C}$	0.5	W
T_{stg}	Storage temperature	-65 to 150	$^\circ\text{C}$
T_{J}	Max. operating junction temperature	150	$^\circ\text{C}$

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	250	$^\circ\text{C}/\text{W}$

Notes:(1)Device mounted on PCB area of 1 cm²

2 Electrical characteristics

($T_{case} = 25^\circ C$ unless otherwise specified)

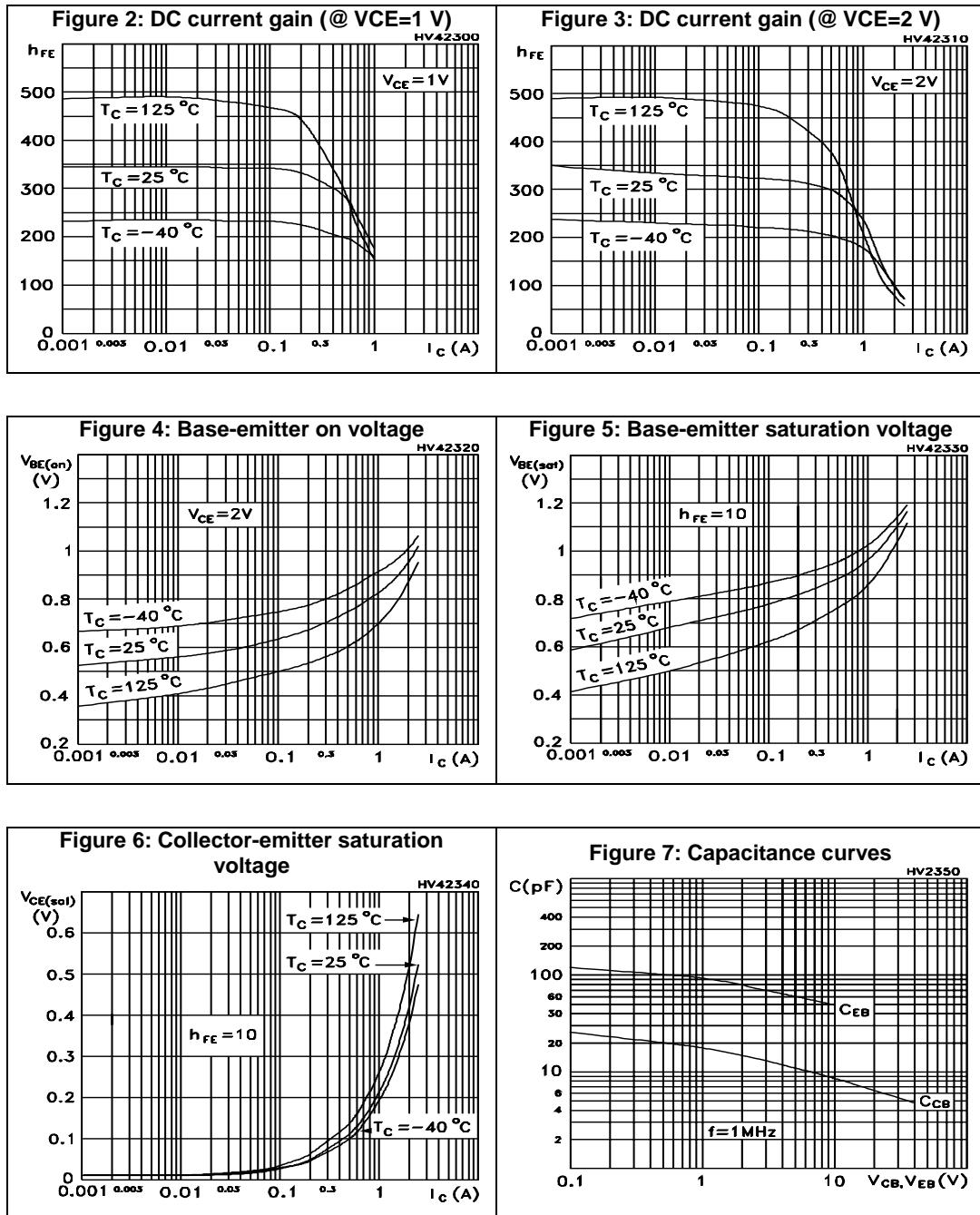
Table 4: Electrical characteristics

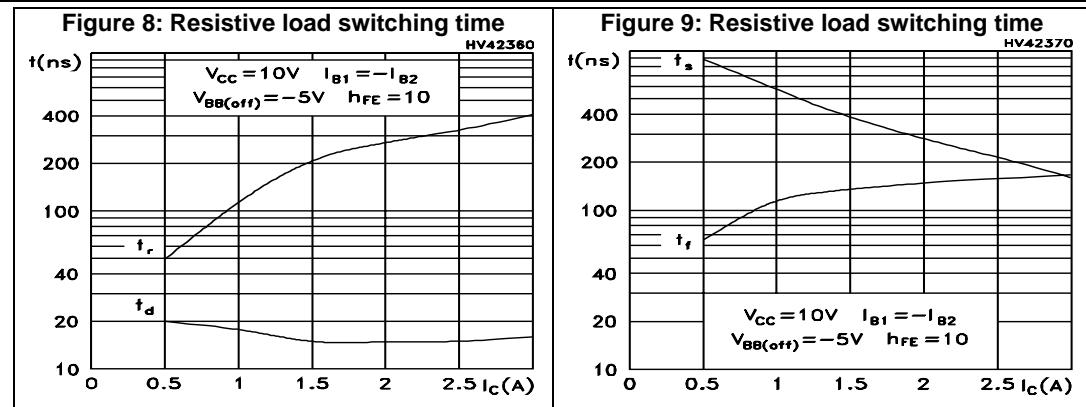
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector cut-off current ($I_E = 0$)	$V_{CB} = 60 V$			0.1	μA
I_{EBO}	Emitter cut-off current ($I_C = 0$)	$V_{EB} = 5 V$			0.1	μA
$V_{(BR)CBO}$	Collector-base breakdown voltage ($I_E = 0$)	$I_C = 100 \mu A$	60			V
$V_{(BR)CEO}^{(1)}$	Collector-emitter breakdown voltage ($I_B = 0$)	$I_C = 10 mA$	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage ($I_C = 0$)	$I_E = 100 \mu A$	5			V
$V_{CE(sat)}$	Collector-emitter saturation voltage	$I_C = 0.5 A I_B = 50 mA$		130	210	mV
		$I_C = 1 A I_B = 100 mA$		210	430	mV
$V_{BE(sat)}$	Base-emitter saturation voltage	$I_C = 1 A I_B = 100 mA$		0.9	1.25	V
h_{FE}	DC current gain	$I_C = 0.5 A V_{CE} = 2V$	180	250	560	
		$I_C = 1 A V_{CE} = 2V$	85	130		
		$I_C = 2 A V_{CE} = 2V$		30		
	Resistive load					
t_{on}	Turn-on time	$I_C = 1.5 A V_{CC} = 10 V$ $I_{B1} = -I_{B2} = 150 mA$ $V_{BB(off)} = -5 V$		220		ns
t_{off}	Turn-off time			500		ns

Notes:

(1)Pulse test: pulse duration = 300 μs , duty cycle $\leq 1.5 \%$

2.1 Typical characteristic (curves)





3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com.
ECOPACK® is an ST trademark.

3.1 SOT-23 mechanical data

Figure 10: SOT-23 mechanical drawing

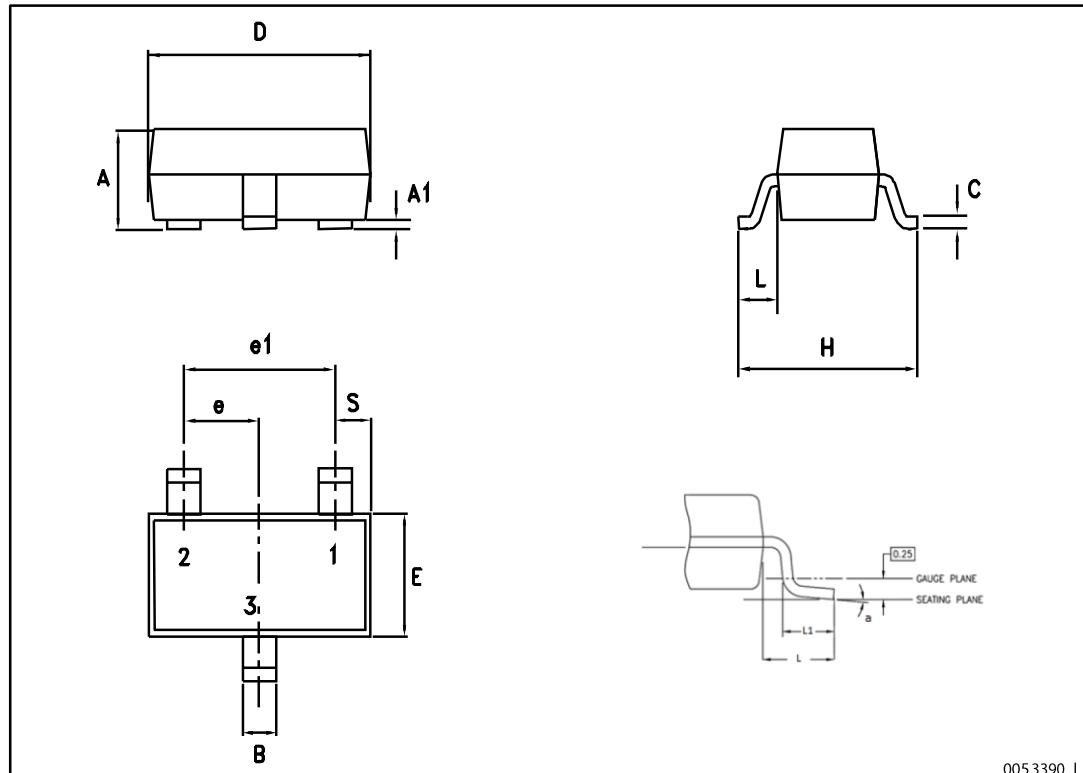
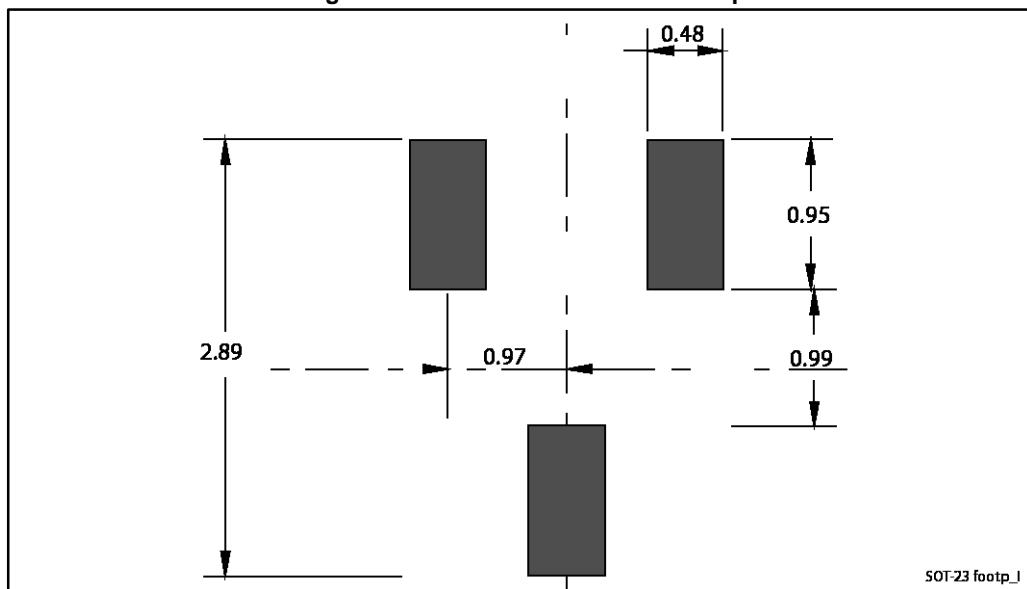


Table 5: SOT-23 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.89		1.40
A1	0		0.10
B	0.30		0.51
C	0.085		0.18
D	2.75		3.04
e	0.85		1.05
e1	1.70		2.10
E	1.20		1.75
H	2.10		3.00
L		0.60	
S	0.35		0.65
L1	0.25		0.55
a	0°		8°

Figure 11: SOT-23 recommended footprint



Dimensions are in mm.

4 Revision history

Table 6: Document revision history

Date	Revision	Changes
12-Feb-2008	1	Initial release
08-May-2014	2	Updated Section 3: "Package mechanical data" .
01-Apr-2015	3	Updated marking in Table 1: "Device summary"